

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AM81214-060** is Designed for 1200 – 1400 MHz, L-Band Applications.

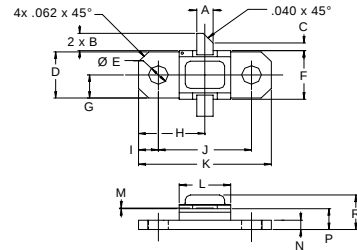
FEATURES:

- Internal Input/Output Matching Network
- $P_G = 6.6$ dB at 55 W/1400 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CC}	32 V
P_{DISS}	107 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+250^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	1.4°C/W

PACKAGE STYLE .310 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.100 / 2.54	.120 / 3.05
C	.050 / 1.27	
D	.286 / 7.26	.306 / 7.77
E	.110 / 2.79	.130 / 3.30
F	.306 / 7.77	.318 / 8.08
G	.148 / 3.76	
H	.400 / 10.16	
I	.119 / 3.02	
J	.552 / 14.02	.572 / 14.53
K	.790 / 20.07	.810 / 20.57
L	.300 / 7.62	.320 / 8.13
M	.003 / 0.08	.006 / 0.15
N	.052 / 1.32	.072 / 1.83
P	.118 / 3.00	.131 / 3.33
R		.230 / 5.84

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20$ mA	55			V
BV_{CER}	$I_C = 40$ mA $R_{BE} = 10 \Omega$	55			V
BV_{EBO}	$I_E = 2$ mA	3.5			V
I_{CES}	$V_{CE} = 28$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 2.0$ A	15		150	---
P_G η_c	$V_{CC} = 28$ V $P_{OUT} = 55$ W $f = 1.2$ to 1.4 GHz	6.6 50			dB %